

# RGTH60TS65

### 650V 30A Field Stop Trench IGBT

| $V_{CES}$                   | 650V |
|-----------------------------|------|
| I <sub>C(100°C)</sub>       | 30A  |
| V <sub>CE(sat) (Typ.)</sub> | 1.6V |
| $P_D$                       | 194W |

### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

### Applications

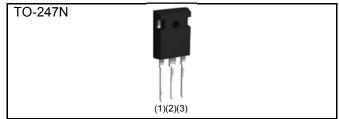
**PFC** 

**UPS** 

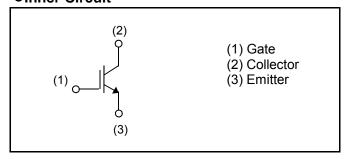
**Power Conditioner** 

ΙH

### Outline



### ●Inner Circuit



Packaging Specifications

|      | Packaging                 | Tube       |
|------|---------------------------|------------|
|      | Reel Size (mm)            | -          |
| Typo | Tape Width (mm)           | -          |
| Туре | Basic Ordering Unit (pcs) | 450        |
|      | Packing code              | C11        |
|      | Marking                   | RGTH60TS65 |

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

| Parameter                      |                        | Symbol             | Value       | Unit |
|--------------------------------|------------------------|--------------------|-------------|------|
| Collector - Emitter Voltage    |                        | V <sub>CES</sub>   | 650         | V    |
| Gate - Emitter Voltage         |                        | $V_{GES}$          | ±30         | V    |
| Collector Current              | T <sub>C</sub> = 25°C  | I <sub>C</sub>     | 58          | А    |
|                                | T <sub>C</sub> = 100°C | I <sub>C</sub>     | 30          | А    |
| Pulsed Collector Current       |                        | I <sub>CP</sub> *1 | 120         | А    |
| Dower Dissipation              | T <sub>C</sub> = 25°C  | P <sub>D</sub>     | 194         | W    |
| Power Dissipation              | T <sub>C</sub> = 100°C | P <sub>D</sub>     | 97          | W    |
| Operating Junction Temperature |                        | T <sub>j</sub>     | -40 to +175 | °C   |
| Storage Temperature            |                        | T <sub>stg</sub>   | -55 to +175 | °C   |

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

### ●Thermal Resistance

| Parameter                               | Symbol            | Values |      |      | Unit  |
|---|-------------------|--------|------|------|-------|
| raiametei                               |                   | Min.   | Тур. | Max. | Offic |
| Thermal Resistance IGBT Junction - Case | $R_{\theta(j-c)}$ | -      | 1    | 0.77 | °C/W  |

## ullet IGBT Electrical Characteristics (at $T_j$ = 25°C unless otherwise specified)

| Parameter                                | Symbol               | Conditions                                       | Values |      |      | Unit  |
|--|----------------------|--|--------|------|------|-------|
| r ai ainetei                             | Syllibol             |  | Min.   | Тур. | Max. | Offic |
| Collector - Emitter Breakdown<br>Voltage | BV <sub>CES</sub>    | $I_{C} = 10 \mu A, V_{GE} = 0 V$                 | 650    | 1    | 1    | V     |
| Collector Cut - off Current              | I <sub>CES</sub>     | V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V     | 1      | 1    | 10   | μΑ    |
| Gate - Emitter Leakage Current           | I <sub>GES</sub>     | $V_{GE} = \pm 30V, V_{CE} = 0V$                  | -      | -    | ±200 | nA    |
| Gate - Emitter Threshold<br>Voltage      | $V_{\text{GE(th)}}$  | $V_{CE} = 5V, I_{C} = 21.0 \text{mA}$            | 4.5    | 5.5  | 6.5  | V     |
| Collector - Emitter Saturation Voltage   | V <sub>CE(sat)</sub> | $I_C = 30A, V_{GE} = 15V$<br>$T_j = 25^{\circ}C$ | -      | 1.6  | 2.1  | V     |
|  |                      | T <sub>j</sub> = 175°C                           | -      | 2.1  | -    |       |

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

| Parameter                        | Symbol              | Conditions                                    | Values      |      |      | Unit  |
|----------------------------------|---------------------|---|-------------|------|------|-------|
| Farameter                        | Syllibol            |   | Min.        | Тур. | Max. | Offic |
| Input Capacitance                | C <sub>ies</sub>    | V <sub>CE</sub> = 30V                         | -           | 1670 | -    |       |
| Output Capacitance               | C <sub>oes</sub>    | V <sub>GE</sub> = 0V                          | -           | 66   | -    | pF    |
| Reverse Transfer Capacitance     | C <sub>res</sub>    | f = 1MHz                                      | -           | 27   | -    |       |
| Total Gate Charge                | $Q_g$               | V <sub>CE</sub> = 300V                        | -           | 58   | -    |       |
| Gate - Emitter Charge            | $Q_{ge}$            | I <sub>C</sub> = 30A                          | -           | 15   | -    | nC    |
| Gate - Collector Charge          | Q <sub>gc</sub>     | V <sub>GE</sub> = 15V                         | -           | 20   | -    |       |
| Turn - on Delay Time             | t <sub>d(on)</sub>  | I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V  | -           | 27   | -    |       |
| Rise Time                        | t <sub>r</sub>      | $V_{GE} = 15V, R_G = 10\Omega$                | -           | 40   | -    | no    |
| Turn - off Delay Time            | t <sub>d(off)</sub> | T <sub>j</sub> = 25°C                         | -           | 105  | -    | ns    |
| Fall Time                        | t <sub>f</sub>      | Inductive Load                                | -           | 47   | -    |       |
| Turn - on Delay Time             | t <sub>d(on)</sub>  | I <sub>C</sub> = 30A, V <sub>CC</sub> = 400V  | -           | 27   | -    |       |
| Rise Time                        | t <sub>r</sub>      | $V_{GE} = 15V, R_{G} = 10\Omega$              | -           | 40   | -    | no    |
| Turn - off Delay Time            | t <sub>d(off)</sub> | T <sub>j</sub> = 175°C                        | -           | 120  | -    | ns    |
| Fall Time                        | t <sub>f</sub>      | Inductive Load                                | -           | 59   | -    |       |
|                                  |                     | I <sub>C</sub> = 120A, V <sub>CC</sub> = 520V |             |      |      |       |
| Reverse Bias Safe Operating Area | RBSOA               | $V_P = 650V, V_{GE} = 15V$                    | FULL SQUARE |      |      | -     |
|                                  |                     | $R_G = 60\Omega, T_j = 175^{\circ}C$          |             |      |      |       |

### **•**Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

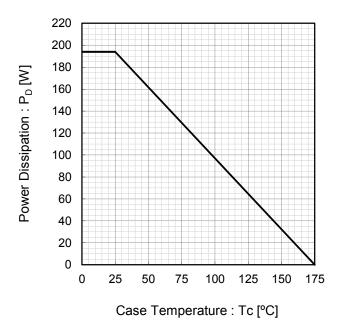


Fig.2 Collector Current vs. Case Temperature

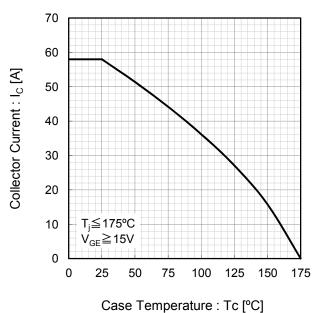
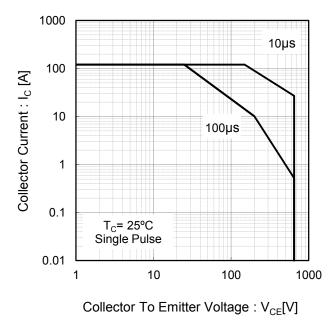


Fig.3 Forward Bias Safe Operating Area



Collector Current :  $I_{\rm C}$  [A]

160
140
120
100
80
60
40
20
T<sub>j</sub>≤175°C
V<sub>GE</sub>=15V
0
0
200
400
600
800

Fig.4 Reverse Bias Safe Operating Area

Collector To Emitter Voltage :  $V_{CE}[V]$ 

#### Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

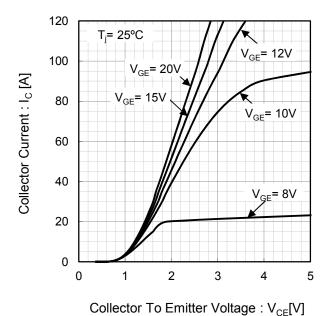
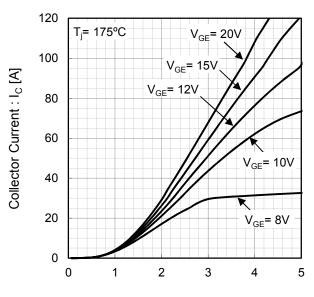


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.7 Typical Transfer Characteristics

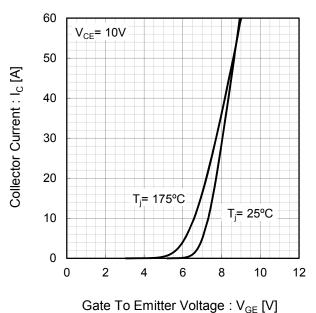
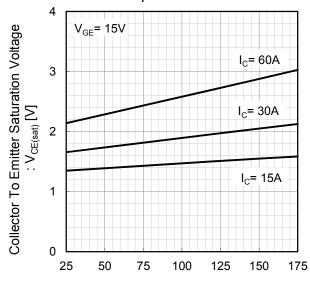


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

#### Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

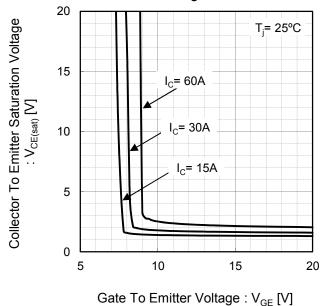
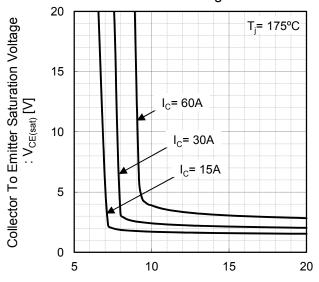


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage :  $V_{GE}[V]$ 

Fig.11 Typical Switching Time vs. Collector Current

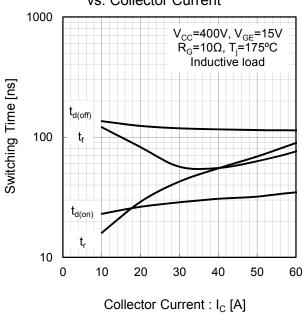
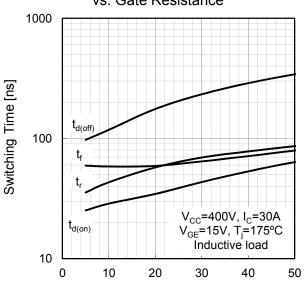


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance :  $R_G[\Omega]$ 

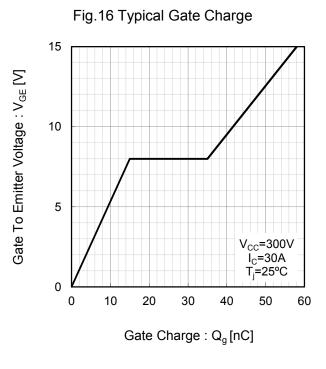
### **•**Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$ 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V R<sub>G</sub>=10 $\Omega$ , T<sub>j</sub>=175°C Inductive load 0.01 0 10 40 60 20 30 50 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=30A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

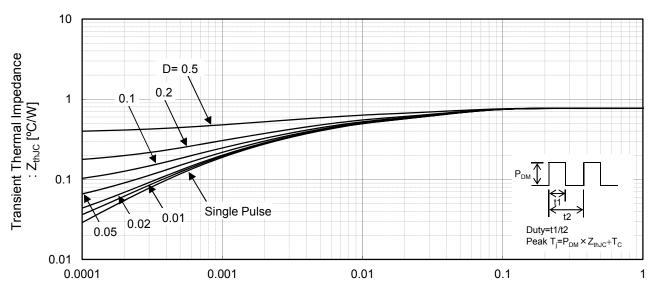
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V<sub>GE</sub>=0V T<sub>i</sub>=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]



### **•**Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

### ●Inductive Load Switching Circuit and Waveform

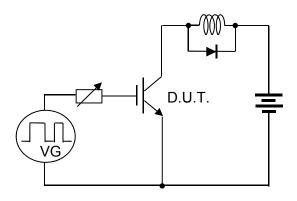


Fig.18 Inductive Load Circuit

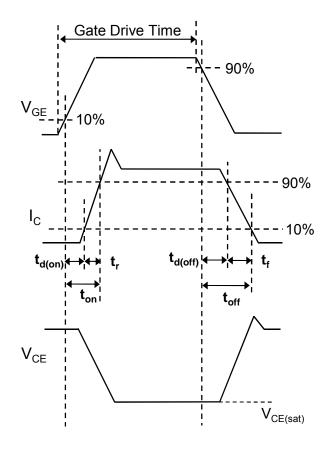


Fig.19 Inductive Load Waveform

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